

MITSUBISHI PSF15S92F6 SiC INTELLIGENT POWER MODULE ANALYSIS REPORT

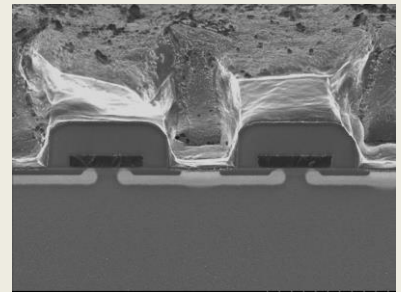
September 2017. LTEC Corporation released a detailed structure and process analysis report of the PSF15S92F6 Dual Inline Package Intelligent Power Module (DIPIPM). This device improves R_{ON} by 70% relative to a conventional Si power device.



Package (Module)



Die (SiC OSFET)



SiC MOSFET cross-section

Device features

- Max. operating voltage : 600V, rated DC Drain current $I_D @ 25^\circ\text{C} = 15\text{A}$
- Very low specific On-resistance, $R_{ON} \times A = 500\text{m}\Omega \times \text{mm}^2$

The report has two individually purchasable sections: Structure Analysis and a Process Analysis sections. The 100-page Structure Analysis section reveals the physical construction of the device, including EDX materials analysis, and many other fine details. The 24-page Process Analysis section includes manufacturing process flow, the estimated number of photomasking steps, and the impurity concentration of the epitaxial layer.

Note: The listed report price may not be accurate as it decreases over time.

Please contact us for current report pricing : info@ltecusa.com

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